

Title (en)

FLUIDIC MICROSYSTEM AND METHOD COMPRISING FIELD-FORMING PASSIVATION LAYERS PROVIDED ON MICROELECTRODES

Title (de)

FLUIDISCHES MIKROSYSTEM UND VERFAHREN MIT FELDFORMENDEN PASSIVIERUNGSSCHICHTEN AUF MIKROELEKTRODEN

Title (fr)

MICROSYSTEME FLUIDIQUE ET PROCEDE COMPORTANT DES COUCHES DE PASSIVATION CREANT DES CHAMPS, APPLIQUEES SUR DES MICROELECTRODES

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Application

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Abstract (en)

[origin: WO2004050252A1] The invention relates to a fluidic microsystem (100) comprising at least one channel (10) through which a particle suspension can flow, and first and second electrode devices (40, 60) which are arranged on first and second channel walls (21, 31) for producing electrical alternating voltage fields in the channel (10). The first electrode device (40) is provided with at least one first structural element (41, 51) for field formation in the channel, and the second electrode device (60) has a flat electrode layer (61) with a closed second electrode surface carrying a second passivation layer (70). The at least one first structural element (41, 51) forms a small active electrode surface as the second electrode surface, and the second passivation layer (70) is a closed layer which fully covers the second electrode layer (61).

IPC 8 full level

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